

Electronic Supplementary Information (ESI)

A facile solution-processed alumina as efficient electron-injection layer for inverted organic light-emitting diodes

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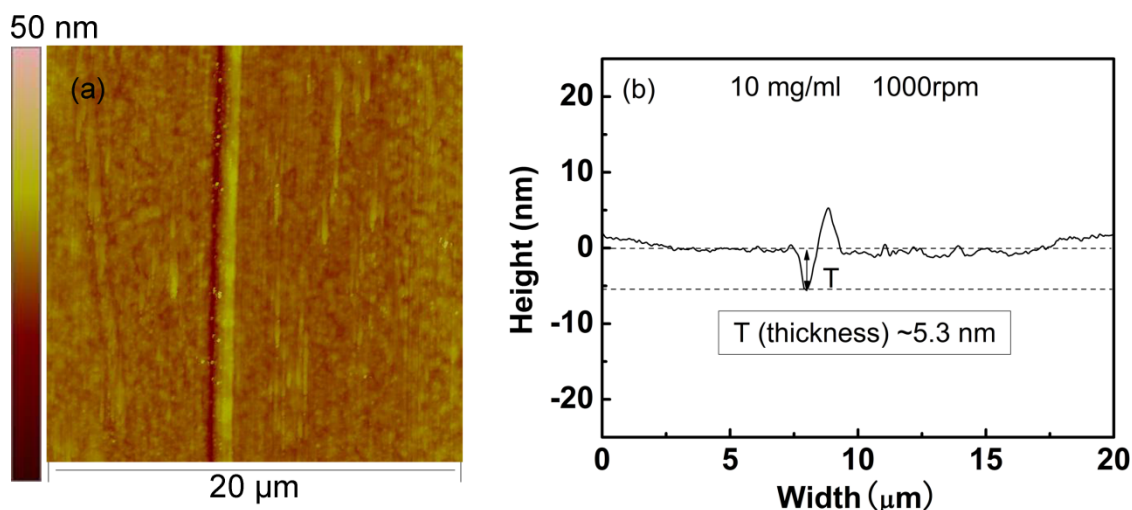


Fig. S 1 a) Surface morphology of the alumina-coated ITO examined by AFM, image scale: 20 μm×20 μm; b) The corresponding line profiling analysis of the alumina-coated ITO. Fabrication: 10 mg/ml alumina precursor solution, spin-casted at 1000 rpm.

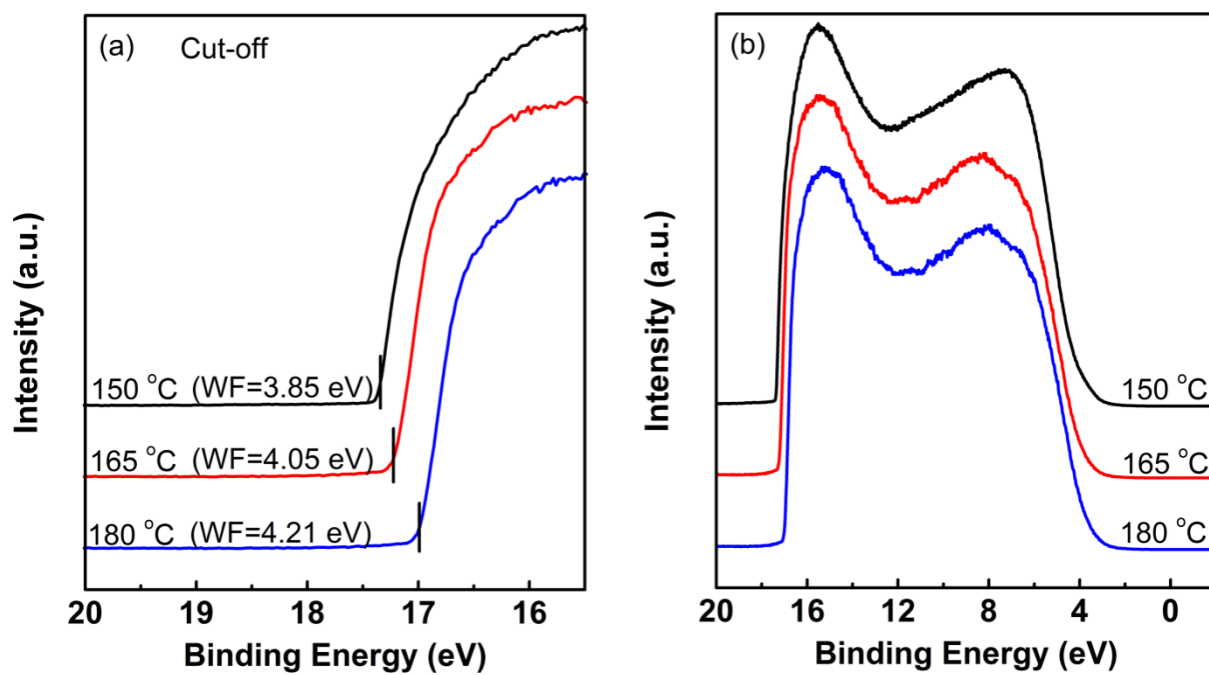


Fig. S 2 a) UPS spectra of ultra-thin alumina-coated ITO as a function of the annealing temperatures; b) UPS full spectra.

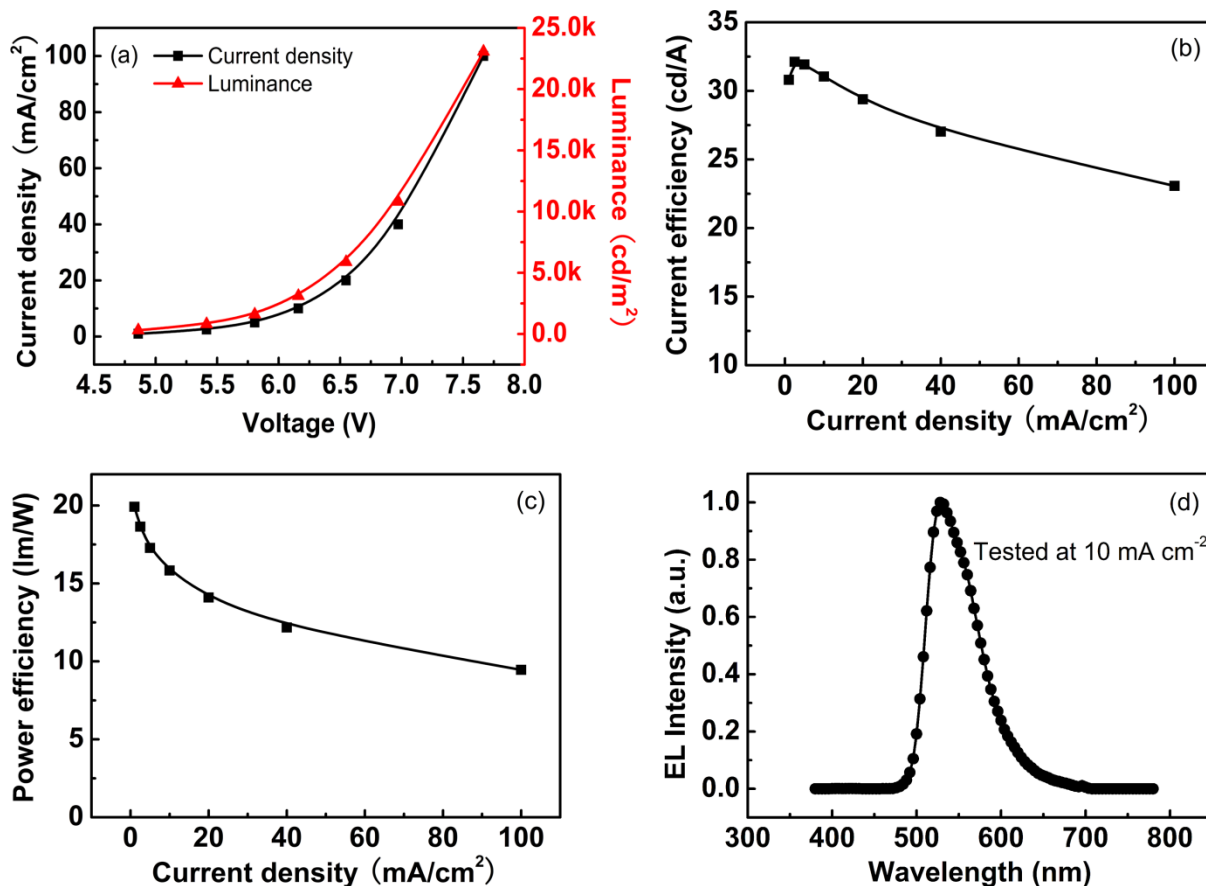


Fig. S 3 Characteristics of a) current density-voltage and luminance-voltage; b) current efficiency-current density; c) power efficiency-current density and d) electroluminescence spectra in the green phosphorescent IOLEDs. Device structure: ITO/Alumina/BPhen:LiF(5nm)/CBP: Ir(ppy)₂(acac)(30nm)/TCTA(30nm)/MoO₃(10nm)/Al. The doping concentration of Ir(ppy)₂(acac) in CBP is about 7% (v/v).